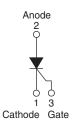


Vishay Semiconductors

Thyristor, Surface Mount, Phase Control SCR, 16 A





TO-263AB (D²PAK)

PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
Diode variation	Single SCR							
I _{T(AV)}	16 A							
V _{DRM} /V _{RRM}	800 V, 1200 V							
V _{TM}	1.25 V							
I _{GT}	45 mA							
TJ	- 40 to 125 °C							

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum (P peak of 260 °C
- Designed and qualified according JEDEC[®]-JESD47
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...S-M3 High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5						
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A					
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0						

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	16	۸						
I _{RMS}		25	A						
V _{RRM} /V _{DRM}		800 to 1200	V						
I _{TSM}		350	А						
V _T	16 A, T _J = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		- 40 to 125	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} ∕I _{DRM} , AT 125 °C mA						
VS-25TTS08S-M3	800	800	10						
VS-25TTS12S-M3	1200	1200	10						

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VS-25TTS08S-M3, VS-25TTS12S-M3 Series

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ABSOLUTE MAXIMUM RATINGS						r			
PARAMETER	SYMBOL	TES	ST CONDITIONS	VAL	UES	UNITS			
	OTHEOL			TYP.	MAX.	onno			
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 93 {}^{\circ}{\rm C}, 180^{\circ}{\rm C}$	conduction half sine wave	1	6				
Maximum RMS on-state current	I _{RMS}			2	5	Α			
Maximum peak, one-cycle,		10 ms sine pulse,	rated V _{RRM} applied	30	00	A			
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	35	50				
Maximum 12t for fueing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	45	50	A ² s			
Maximum I ² t for fusing	1-1	10 ms sine pulse,	63	30	A-S				
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 m	6300		A²√s				
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C			25	V			
On-state slope resistance	r _t	T 105 %C		12	2.0	mΩ			
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1.0		V			
	1 /1	T _J = 25 °C	V Detect V V	0.	.5				
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	V _R = Rated V _{RRM} /V _{DRM}	10					
Holding current	I _H	VS-25TTS08, VS-25TTS12	resistive load initial I _T – 1 A		150	mA			
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$			Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		20	00]
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max., lines$	ar to 80 %, $V_{DRM} = R_g - k = Open$	50	00	V/µs			
Maximum rate of rise of turned-on current	dl/dt				50	A/µs			

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	vv
Maximum peak positive gate current	+ I _{GM}		1.5	А
Maximum peak negative gate voltage	- V _{GM}		10	V
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -10 \ ^{\circ}C$	60	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45	mA
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20	
		Anode supply = 6 V, resistive load, $T_J = -10 \degree C$	2.5	
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V
Maximum DC gate voltage not to trigger	V _{GD}		0.25	
Maximum DC gate current not to trigger	I _{GD}	$T_J = 125 \text{ °C}, V_{DRM} = Rated value$	2.0	mA

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T 125 °C	4	μs				
Typical turn-off time	t _q	T _J = 125 °C	110					

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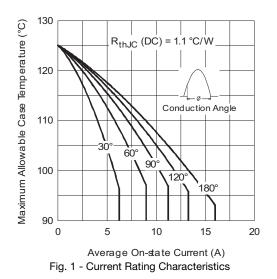
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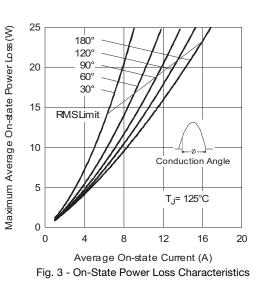
THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C			
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W			
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	0/11			
Approximate weight			2	g			
Approximate weight			0.07	OZ.			
Marking device		Case style D ² PAK (SMD-220)	25TT	S08S			
		Case sigle D-FAR (SIVID-220)	25TT	S12S			

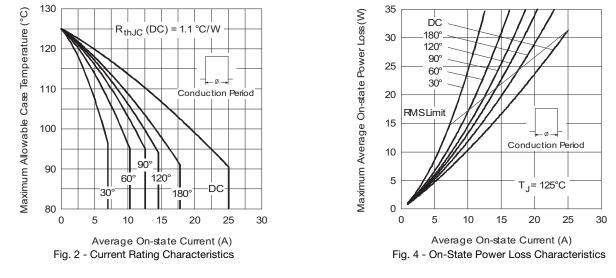
Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W

For recommended footprint and soldering techniques refer to application note #AN-994







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3

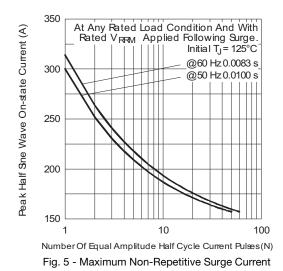
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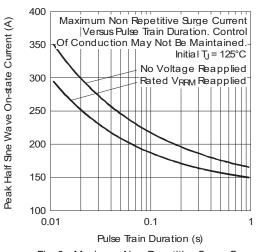
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VS-25TTS08S-M3, VS-25TTS12S-M3 Series

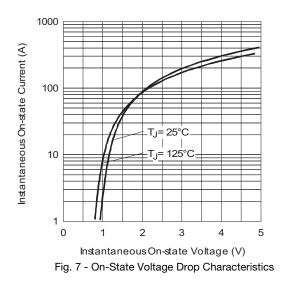
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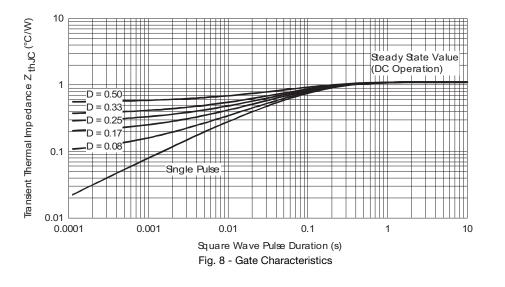
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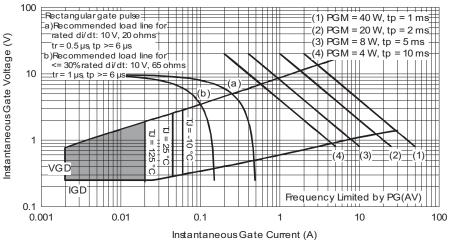


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	25	т	т	S	12	S	TRL	-M3	
	1	2	3	4	5	6	7	8	9	
	1	- Vis	hay Sen	nicondu	ctors pro	oduct				
	2	- Current rating (25 = 25 A)								
	3		Fircuit configuration:							
	4		kage:	2						
	5	- Тур	D ² PAK e of silio	con:	ony roct	ifior			08 = 80	200 1
	6		S = Standard recovery rectifier Voltage rating: Voltage code x 100 = V _{RRM} ———					12 = 1		
	7	- S = Surface mountable								
	8	• TI • TI	R = Ta	be and rope and r	eel (righ	nt orient	ed)			
	9	M3	s = Halo	gen-free	e, RoHS	-compli	ant, and	termina	ations le	ad (F

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-25TTS08S-M3	50	1000	Antistatic plastic tubes						
VS-25TTS08STRR-M3	800	800	13" diameter reel						
VS-25TTS08STRL-M3	800	800	13" diameter reel						
VS-25TTS12S-M3	50	1000	Antistatic plastic tubes						
VS-25TTS12STRR-M3	800	800	13" diameter reel						
VS-25TTS12STRL-M3	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95444						
Packaging information	www.vishay.com/doc?95032						

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Outline Dimensions

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D²PAK



Conforms to JEDEC outline D²PAK (SMD-220) в Pad layout (2)(3)A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 (|(0.38)^{MIN.} (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.15)^{0.01} Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Г 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" 3. - Anode

Rotated 90 °CW Scale: 8:1

SYMBOL	MILLIMETERS		INCHES		NOTES		NOTES		S NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES				
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3				
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3				
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3				
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC					
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625					
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110					
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3				
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070					
c2	1.14	1.65	0.045	0.065			L3	L3 0.25 BSC		0.010	BSC					
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208					

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

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DIMENSIONS in millimeters and inches



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